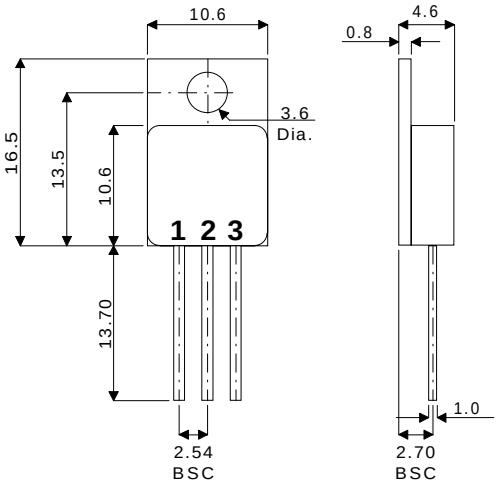
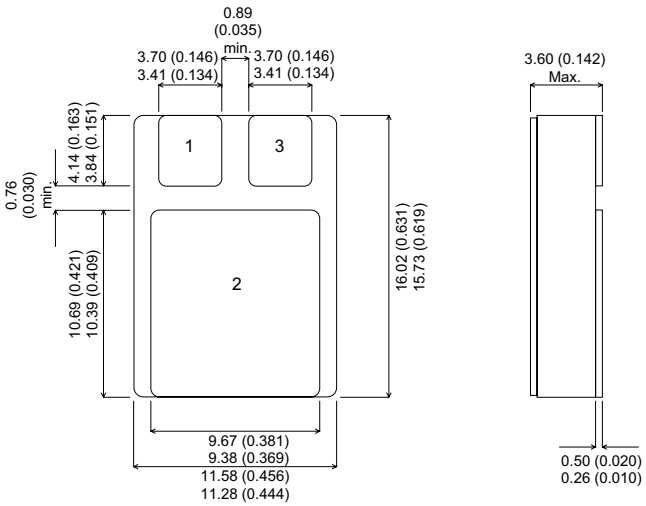
BDS16 BDS16SMD
BDS17 BDS17SMD

MECHANICAL DATA
Dimensions in mm





SILICON NPN EPITAXIAL BASE IN TO220 METAL AND SMD1 CERAMIC SURFACE MOUNT PACKAGES

FEATURES

- **HERMETIC METAL OR CERAMIC PACKAGES**
- **HIGH RELIABILITY**
- **MILITARY AND SPACE OPTIONS**
- **SCREENING TO CECC LEVELS**
- **FULLY ISOLATED (METAL VERSION)**

APPLICATIONS

- **POWER LINEAR AND SWITCHING APPLICATIONS**
- **GENERAL PURPOSE POWER**

TO220M - TO220 Metal Package - Isolated
SMD1 - Ceramic Surface Mount Package

Pin 1 – Base **Pin 2** – Collector **Pin 3** – Emitter

ABSOLUTE MAXIMUM RATINGS (T_{case}=25°C unless otherwise stated)		**BDS16**	**BDS17**
V_{CBO}	Collector - Base voltage (I_E = 0)	120V	150V
V_{CEO}	Collector - Emitter voltage (I_B = 0)	120V	150V
V_{EBO}	Emitter - Base voltage (I_C = 0)	5V	
I_E , I_C	Emitter , Collector current	8A	
I_B	Base current	2A	
P_{tot}	Total power dissipation at $T_{case} \leq 75°C$	50W	
T_{stg}	Storage Temperature	–65 TO 200°C	
T_j	Junction Temperature	200°C	

Semelab plc. Telephone +44(0)1455 556565. Fax +44(0)1455 552612.
E-mail: sales@semelab.co.uk Website: http://www.semelab.co.uk

BDS16 BDS16SMD
BDS17 BDS17SMD

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current (I_E = 0)	**BDS16** **BDS17**	V_{CB} = 120V V_{CB} = 150V			20 20	µA
I_{CEO}	Collector cut-off current (I_B = 0)	**BDS16** **BDS17**	V_{CE} = 60V V_{CE} = 75V			0.1 0.1	mA
I_{EBO}	Emitter cut-off current (I_C = 0)	V_{EB} = 5V				10	µA
$V_{CEO(sus)}$*	Collector - Emitter sustaining voltage (I_B = 0)	**BDS16** **BDS17**	I_C = 100mA	120 150			V
$V_{CE(sat)}$*	Collector - Emitter saturation voltage	I_C = 1A	I_B = 0.1A			0.5	V V
$V_{BE(on)}$*	Base - Emitter voltage	I_C = 1A	V_{CE} = 2V			1.0	V
h_{FE}*	DC Current gain	I_C = 0.5A I_C = 4A	V_{CE} = 2V V_{CE} = 2V	40 15		250 150	
f_T	Transition frequency	I_C = 0.5A	V_{CE} = 10V	30			MHz

*Pulsed : Pulse duration = 300 µs , duty cycle = 1.5%

SWITCHING CHARACTERISTICS

	Parameter	Test Conditions	Max.	Unit
t_{on}	On Time (t_d + t_r)	I_C = 2A V_{CC} = 80V I_{B1} = 0.2A	0.5	µs
t_s	Storage Time	I_C = 2A V_{CC} = 80V I_{B1} = –I_{B2} = 0.2A	3.0	µs
t_f	Fall Time		0.4	µs

THERMAL DATA

$R_{THj\text{-}case}$	Thermal resistance junction - case	Max. 2.5°C/W
$R_{THj\text{-}a}$	Thermal resistance junction - ambient	Max. 62.5°C/W